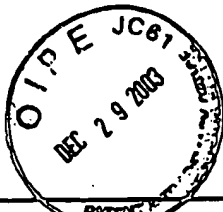
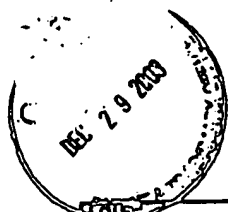




SHEET 1 OF 1

FORM PTO - 1449				ATTORNEY DOCKET NO.: ASC-058A					
SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT				APPLICANTS: Leitz <i>et al.</i>					
				SERIAL NO.: 10/647,074					
				FILING DATE: August 22, 2003					
				GROUP: 2812 2823					
U.S. PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE		
Le	A176	5,387,796	02/07/1995	Joshi <i>et al.</i>	1				
Le	A177	5,434,102	07/18/1995	Watanabe <i>et al.</i>	1				
FOREIGN PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
Le	B49	2-210816	08/22/1990	JP				N	Abstract
Le	B50	3-36717	02/18/1991	JP				N	Abstract
Le	B51	61-14116	06/28/1986	JP				N	Abstract
OTHER ART, JOURNAL ARTICLES, ETC.									
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
Le	C132	Feichtinger <i>et al.</i> , "Misfit Dislocation Nucleation Study in p/p+ Silicon," <u>Journal of the Electrochemical Society</u> , 148 (7) (2001), pp. G379-G382.							
	C133	Grillot <i>et al.</i> , "Acceptor diffusion and segregation in (Al _x Ga _{1-x}) _{0.5} In _{0.5} P heterostructures," <u>Journal of Applied Physics</u> , Vol. 91, No. 8 (April 15, 2002), pp. 4891-4899.							
	C134	Hsu <i>et al.</i> , "Surface morphology of related GexSi _{1-x} films," <u>Applied Physics Letters</u> , 61 (11) (September 14, 1992), pp. 1293-1295.							
Le	C135	"How to Make Silicon," Wacker University, http://www.wafernet.com/PresWK/h-ptl-as3_wsc_siltronic_com_pages_training_pages_Silic... , August 28, 2002.							
EXAMINER					DATE CONSIDERED 9/23/04				

3003691



FORM PTO - 1449

INFORMATION DISCLOSURE STATEMENT

ATTORNEY DOCKET NO.: ASC-058A

APPLICANT(S): Leitz *et al.*

SERIAL NO.: 10/647,074

FILING DATE: August 22, 2003 GROUP: ~~2842~~ 2823

U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
Lee	A1	2001/0003364	06/14/2001	Sugawara <i>et al.</i>			
	A2	2001/0014570	08/16/2001	Wenski <i>et al.</i>			
	A3	2002/0043660	04/18/2002	Yamazaki <i>et al.</i>			
	A4	2002/0052084	05/02/2002	Fitzgerald			
	A5	2002/0084000	07/04/2002	Fitzgerald			
	A6	2002/0096717	07/25/2002	Chu <i>et al.</i>			
	A7	2002/0100942	08/01/2002	Fitzgerald <i>et al.</i>			
	A8	2002/0123167	09/05/2002	Fitzgerald			
	A9	2002/0123183	09/05/2002	Fitzgerald			
	A10	2002/0123197	09/05/2002	Fitzgerald <i>et al.</i>			
	A11	2002/0125471	09/12/2002	Fitzgerald <i>et al.</i>			
	A12	2002/0125497	09/12/2002	Fitzgerald			
	A13	2002/0168864	11/14/2002	Cheng <i>et al.</i>			
	A14	2002/0185686	12/12/2002	Christiansen <i>et al.</i>			
	A15	2003/0003679	01/02/2003	Doyle <i>et al.</i>			
	A16	2003/0013323	01/16/2003	Hammond <i>et al.</i>			
	A17	2003/0025131	02/06/2003	Lee <i>et al.</i>			
	A18	2003/0034529	02/20/2003	Fitzgerald <i>et al.</i>			
	A19	2003/0041798	03/06/2003	Wenski <i>et al.</i>			
	A20	2003/0057439	03/27/2003	Fitzgerald			
	A21	2003/0077867	04/24/2003	Fitzgerald			
	A22	2003/0102498	06/05/2003	Braithwaite <i>et al.</i>			
	A23	2003/0127646	07/10/2003	Christiansen <i>et al.</i>			
	A24	2003/0186073	10/02/2003	Fitzgerald			03/18/2003
Lee	A25	4,010,045	03/01/1977	Ruehrwein			
EXAMINER <i>Lee</i>				DATE CONSIDERED 9/23/04			



FORM PTO - 1449

INFORMATION DISCLOSURE STATEMENT

ATTORNEY DOCKET NO.: ASC-058A

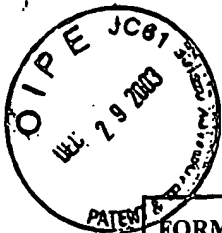
APPLICANT(S): Leitz *et al.*

SERIAL NO.: 10/647,074

FILING DATE: August 22, 2003 GROUP: 2812-2823

U.S. PATENT DOCUMENTS

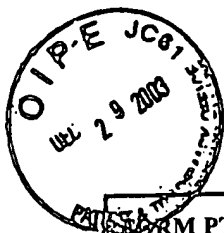
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
Lee	A26	4,710,788	12/01/1987	Dambkes <i>et al.</i>			
	A27	4,900,372	12/13/1990	Lee <i>et al.</i>			
	A28	4,987,462	01/22/1991	Kim <i>et al.</i>			
	A29	4,990,979	02/05/1991	Otto			
	A30	4,997,776	03/05/1991	Haramé <i>et al.</i>			
	A31	5,013,681	05/07/1991	Godbey <i>et al.</i>			
	A32	5,091,767	02/25/1992	Bean <i>et al.</i>			
	A33	5,097,630	03/24/1992	Maeda <i>et al.</i>			
	A34	5,155,571	10/13/1992	Wang <i>et al.</i>			
	A35	5,159,413	10/27/1992	Calviello <i>et al.</i>			
	A36	5,166,084	11/24/1992	Pfiester			
	A37	5,177,583	01/05/1993	Endo <i>et al.</i>			
	A38	5,202,284	04/13/1993	Kamins <i>et al.</i>			
	A39	5,207,864	05/04/1993	Bhat <i>et al.</i>			
	A40	5,208,182	05/04/1993	Narayan <i>et al.</i>			
	A41	5,210,052	05/11/1993	Takasaki			
	A42	5,212,110	05/18/1993	Pfiester <i>et al.</i>			
	A43	5,221,413	06/22/1993	Brasen <i>et al.</i>			
	A44	5,241,197	08/31/1993	Murakami <i>et al.</i>			
	A45	5,250,445	10/05/1993	Bean <i>et al.</i>			
	A46	5,252,173	10/12/1993	Inoue			
	A47	5,279,687	01/18/1994	Tuppen <i>et al.</i>			
	A48	5,285,086	02/08/1994	Fitzgerald			
	A49	5,291,439	03/01/1994	Kauffmann <i>et al.</i>			
	A50	5,298,452	03/29/1994	Meyerson			
Lee	A51	5,308,444	05/03/1994	Fitzgerald <i>et al.</i>			
EXAMINER <i>Lee</i>				DATE CONSIDERED 9/23/04			



FORM PTO - 1449	ATTORNEY DOCKET NO.: ASC-058A
INFORMATION DISCLOSURE STATEMENT	APPLICANT(S): Leitz <i>et al.</i>
	SERIAL NO.: 10/647,074
	FILING DATE: August 22, 2003 GROUP: 2812-2823

U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
✓	A52	5,310,451	05/10/1994	Tejwani <i>et al.</i>			
	A53	5,316,958	05/31/1994	Meyerson			
	A54	5,346,848	09/13/1994	Gruppen- Shemansky <i>et al.</i>			
	A55	5,374,564	12/20/1994	Bruel			
	A56	5,399,522	03/21/1995	Ohori			
	A57	5,413,679	05/09/1995	Godbey			
	A58	5,424,243	06/13/1995	Takasaki			
	A59	5,425,846	06/20/1995	Koze <i>et al.</i>			
	A60	5,426,069	06/20/1995	Selvakumar <i>et al.</i>			
	A61	5,426,316	06/20/1995	Mohammad			
	A62	5,442,205	08/15/1995	Brasen <i>et al.</i>			
	A63	5,461,243	10/24/1995	Ek <i>et al.</i>			
	A64	5,461,250	10/24/1995	Burghartz <i>et al.</i>			
	A65	5,462,883	10/31/1995	Dennard <i>et al.</i>			
	A66	5,476,813	12/19/1995	Naruse			
	A67	5,479,033	12/26/1995	Baca <i>et al.</i>			
	A68	5,484,664	01/16/1996	Kitahara <i>et al.</i>			
	A69	5,523,243	06/04/1996	Mohammad			
	A70	5,523,592	06/04/1996	Nakagawa <i>et al.</i>			
	A71	5,534,713	07/09/1996	Ismail <i>et al.</i>			
	A72	5,536,361	07/16/1996	Kondo <i>et al.</i>			
	A73	5,540,785	07/30/1996	Dennard <i>et al.</i>			
	A74	5,596,527	01/21/1997	Tomioka <i>et al.</i>			
	A75	5,617,351	04/01/1997	Bertin <i>et al.</i>			
	A76	5,630,905	05/20/1997	Lynch <i>et al.</i>			
	A77	5,633,516	05/27/1997	Mishima <i>et al.</i>			
Lee	A78	5,659,187	08/19/1997	Legoues <i>et al.</i>			
EXAMINER					DATE CONSIDERED	9/23/04	



FORM PTO - 1449

INFORMATION DISCLOSURE STATEMENT

ATTORNEY DOCKET NO.: ASC-058A

APPLICANT(S): Leitz *et al.*

SERIAL NO.: 10/647,074

FILING DATE: August 22, 2003 GROUP: 2812-2823

U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
Lee	A79	5,683,934	11/04/1997	Candelaria			
	A80	5,698,869	12/16/1997	Yoshimi <i>et al.</i>			
	A81	5,714,777	02/03/1998	Ismail <i>et al.</i>			
	A82	5,728,623	03/17/1998	Mori			
	A83	5,739,567	04/14/1998	Wong			
	A84	5,759,898	06/02/1998	Ek <i>et al.</i>			
	A85	5,777,347	07/07/1998	Bartelink			
	A86	5,786,612	07/28/1998	Otani <i>et al.</i>			
	A87	5,786,614	07/28/1998	Chuang <i>et al.</i>			
	A88	5,792,679	08/11/1998	Nakato			
	A89	5,801,085	09/01/1998	Kim <i>et al.</i>			
	A90	5,808,344	09/15/1998	Ismail <i>et al.</i>			
	A91	5,810,924	09/22/1998	Legoues <i>et al.</i>			
	A92	5,828,114	10/27/1998	Kim <i>et al.</i>			
	A93	5,847,419	12/08/1998	Imai <i>et al.</i>			
	A94	5,859,864	01/12/1999	Jewell			
	A95	5,877,070	03/02/1999	Goesele <i>et al.</i>			
	A96	5,891,769	04/06/1999	Liaw <i>et al.</i>			
	A97	5,906,708	05/25/1999	Robinson <i>et al.</i>			
	A98	5,906,951	05/25/1999	Chu <i>et al.</i>			
	A99	5,912,479	06/15/1999	Mori <i>et al.</i>			
	A100	5,943,560	08/24/1999	Chang <i>et al.</i>			
	A101	5,963,817	10/05/1999	Chu <i>et al.</i>			
	A102	5,966,622	10/12/1999	Levine <i>et al.</i>			
	A103	5,998,807	12/07/1999	Lustig <i>et al.</i>			
	A104	6,010,937	01/04/2000	Karam <i>et al.</i>			
	A105	6,013,134	01/11/2000	Chu <i>et al.</i>			
Lee	A106	6,030,884	02/29/2000	Mori			
	A107	6,033,974	03/07/2000	Henley <i>et al.</i>			
EXAMINER	Lee			DATE CONSIDERED	9/23/04		



FORM PTO - 1449

INFORMATION DISCLOSURE STATEMENT

ATTORNEY DOCKET NO.: ASC-058A

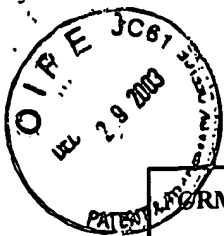
APPLICANT(S): Leitz *et al.*

SERIAL NO.: 10/647,074

FILING DATE: August 22, 2003 GROUP: 2812-2823

U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
See	A108	6,033,995	03/07/2000	Muller			
	A109	6,039,803	03/21/2000	Fitzgerald <i>et al.</i>			
	A110	6,058,044	05/02/2000	Sugiura <i>et al.</i>			
	A111	6,059,895	05/09/2000	Chu <i>et al.</i>			
	A112	6,074,919	06/13/2000	Gardner <i>et al.</i>			
	A113	6,096,590	08/01/2000	Chan <i>et al.</i>			
	A114	6,103,559	08/15/2000	Gardner <i>et al.</i>			
	A115	6,107,653	08/22/2000	Fitzgerald			
	A116	6,111,267	08/29/2000	Fischer <i>et al.</i>			
	A117	6,117,750	09/12/2000	Bensahel <i>et al.</i>			
	A118	6,124,614	09/26/2000	Ryum <i>et al.</i>			
	A119	6,130,453	10/10/2000	Mei <i>et al.</i>			
	A120	6,133,799	10/17/2000	Favors <i>et al.</i>			
	A121	6,140,687	10/31/2000	Shimomura <i>et al.</i>			
	A122	6,143,636	11/07/2000	Forbes <i>et al.</i>			
	A123	6,153,495	11/28/2000	Kub <i>et al.</i>			
	A124	6,154,475	11/28/2000	Soref <i>et al.</i>			
	A125	6,160,303	12/12/2000	Fattaruso			
	A126	6,162,688	12/19/2000	Gardner <i>et al.</i>			
	A127	6,184,111	02/06/2001	Henley <i>et al.</i>			
	A128	6,191,006	02/20/2001	Mori			
	A129	6,191,007	02/20/2001	Matsui <i>et al.</i>			
	A130	6,191,432	02/20/2001	Sugiyama <i>et al.</i>			
	A131	6,194,722	02/27/2001	Fiorini <i>et al.</i>			
	A132	6,204,529	03/20/2001	Lung <i>et al.</i>			
	A133	6,207,977	03/27/2001	Augusto			
	A134	6,210,988	04/03/2001	Howe <i>et al.</i>			
	A135	6,218,677	04/17/2001	Broekaert			
	A136	6,232,138	05/15/2001	Fitzgerald <i>et al.</i>			
See	A137	6,235,567	05/22/2001	Huang			
EXAMINER <i>See</i>				DATE CONSIDERED <i>9/23/04</i>			



FORM PTO - 1449				ATTORNEY DOCKET NO.: ASC-058A			
INFORMATION DISCLOSURE STATEMENT				APPLICANT(S): Leitz <i>et al.</i>			
				SERIAL NO.: 10/647,074			
				FILING DATE: August 22, 2003 GROUP: 2812-5823			
U.S. PATENT DOCUMENTS							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
Lee	A138	6,242,324	06/05/2001	Kub <i>et al.</i>			
	A139	6,249,022	06/19/2001	Lin <i>et al.</i>			
	A140	6,251,755	06/26/2001	Furukawa <i>et al.</i>			
	A141	6,261,929	07/17/2001	Gehrke <i>et al.</i>			
	A142	6,266,278	07/24/2001	Harari <i>et al.</i>			
	A143	6,271,551	08/07/2001	Schmitz <i>et al.</i>			
	A144	6,271,726	08/07/2001	Fransis <i>et al.</i>			
	A145	6,291,321	09/18/2001	Fitzgerald			
	A146	6,313,016	11/06/2001	Kibbel <i>et al.</i>			
	A147	6,316,301	11/13/2001	Kant			
	A148	6,323,108	11/27/2001	Kub <i>et al.</i>			
	A149	6,329,063	12/11/2001	Lo <i>et al.</i>			
	A150	6,335,546	01/01/2002	Tsuda <i>et al.</i>			
	A151	6,339,232	01/15/2002	Takagi			
	A152	6,350,993	02/26/2002	Chu <i>et al.</i>			
	A153	6,368,733	04/09/2002	Nishinaga			
	A154	6,372,356	04/16/2002	Thornton <i>et al.</i>			
	A155	6,399,970	06/04/2002	Kubo <i>et al.</i>			
	A156	6,403,975	06/11/2002	Brunner <i>et al.</i>			
	A157	6,406,589	06/18/2002	Yanagisawa			
	A158	6,407,406	06/18/2002	Tezuka			
	A159	6,420,937	07/16/2002	Akatsuka <i>et al.</i>			
	A160	6,425,951	07/30/2002	Chu <i>et al.</i>			
	A161	6,429,061	08/06/2002	Rim			
	A162	6,482,749	11/19/2002	Billington <i>et al.</i>			
	A163	6,503,773	01/07/2003	Fitzgerald			
	A164	6,515,335	02/04/2003	Christiansen <i>et al.</i>			
Lee	A165	6,518,644	02/11/2003	Fitzgerald			
EXAMINER <i>Lee</i>				DATE CONSIDERED 9/23/04			

FORM PTO - 1449

ATTORNEY DOCKET NO.: ASC-058A

INFORMATION DISCLOSURE STATEMENT

APPLICANT(S): Leitz *et al.*

SERIAL NO.: 10/647,074

FILING DATE: August 22, 2003 GROUP: 2812 2823

U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
Le	A166	6,521,041	02/18/2003	Wu <i>et al.</i>			
	A167	6,525,338	02/25/2003	Mizushima <i>et al.</i>			
	A168	6,555,839	04/29/2003	Fitzgerald			
	A169	6,573,126	06/03/2003	Cheng <i>et al.</i>			
	A170	6,576,532	06/10/2003	Jones <i>et al.</i>			
	A171	6,583,015	06/24/2003	Fitzgerald <i>et al.</i>			
	A172	6,593,191	07/15/2003	Fitzgerald			
	A173	6,594,293	07/15/2003	Bulsara <i>et al.</i>			
	A174	6,602,613	08/05/2003	Fitzgerald			
Le	A175	6,603,156	08/05/2003	Rim			

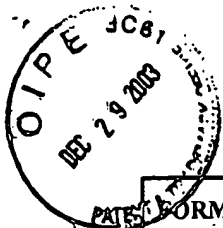
FOREIGN PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
Le	B1	41 01 167 /	07/23/1992	DE				N	Abstract
	B2	0 514 018 /	11/19/1992	EP				N	Y
	B3	0 587 520 /	03/16/1994	EP				N	Y
	B4	0 683 522 /	11/22/1995	EP				N	Y
	B5	0 828 296 /	03/11/1998	EP				N	Y
	B6	0 829 908 /	03/18/1998	EP				N	Y
	B7	0 838 858 /	04/29/1998	EP				N	Abstract
	B8	1 020 900 /	07/19/2000	EP				N	Y
	B9	1 174 928 /	01/23/2002	EP				N	Y
	B10	2 342 777 /	04/19/2000	GB				Y	Y
Le	B11	4-307974 /	10/30/1992	JP				N	Abstract

EXAMINER

DATE CONSIDERED

9/23/04



PATENT FORM PTO - 1449	ATTORNEY DOCKET NO.: ASC-058A
INFORMATION DISCLOSURE STATEMENT	APPLICANT(S): Leitz <i>et al.</i>
	SERIAL NO.: 10/647,074
	FILING DATE: August 22, 2003 GROUP: 2842-2827

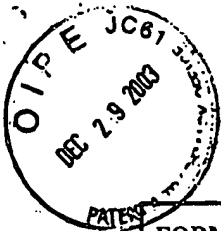
FOREIGN PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
Lee	B12	5-166724	07/02/1993	JP				N	Abstract
	B13	6-177046	06/24/1994	JP				N	Abstract
	B14	6-244112	09/02/1994	JP				Y	Y
	B15	6-252046	09/09/1994	JP				Y	Y
	B16	7-94420	04/07/1995	JP				N	Abstract
	B17	7-106446	04/21/1995	JP				N	Abstract
	B18	7-240372	09/12/1995	JP				N	Abstract
	B19	10-270685	10/09/1998	JP				N	Y
	B20	11-233744	08/27/1999	JP				N	Abstract
	B21	63-73398	04/02/1988	JP				N	N
	B22	2000-021783	01/21/2000	JP				N	Y
	B23	2000-031491	01/28/2000	JP				N	Y
	B24	2000-513507	10/10/2000	JP				Y	Y
	B25	2001-319935	11/16/2001	JP				N	Y
	B26	2002-076334	03/15/2002	JP				N	Y
	B27	2002-164520	06/07/2002	JP				N	Y
	B28	2002-289533	10/04/2002	JP				N	Y
	B29	2002-356399	12/13/2002	JP				N	Y
	B30	2003-520444	07/02/2003	JP				N	Abstract
	B31	98/59365	12/30/1998	WO				N	Y
	B32	99/53539	10/21/1999	WO				N	Y
	B33	00/48239	08/17/2000	WO				N	Y
	B34	00/54338	09/14/2000	WO				N	Y
	B35	01/022482	03/29/2001	WO				N	Y
Lee	B36	01/54175	07/26/2001	WO				N	Y

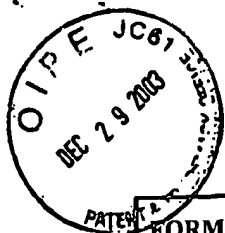
EXAMINER

DATE CONSIDERED

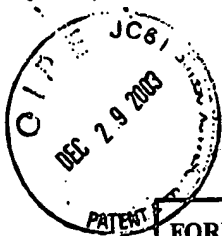
9/23/04



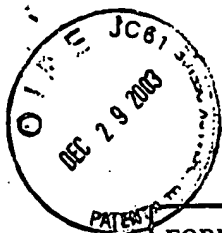
FORM PTO - 1449					ATTORNEY DOCKET NO.: ASC-058A				
INFORMATION DISCLOSURE STATEMENT					APPLICANT(S): Leitz <i>et al.</i>				
					SERIAL NO.: 10/647,074				
					FILING DATE: August 22, 2003 GROUP: 2812-2823				
FOREIGN PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
Lee	B37	01/54202	07/26/2001	WO				N	Y
	B38	01/93338	12/06/2001	WO				N	Y
	B39	01/99169	12/27/2001	WO				N	Y
	B40	02/071488	09/12/2002	WO				N	Y
	B41	02/071491	09/12/2002	WO				N	Y
	B42	02/071495	09/12/2002	WO				N	Y
	B43	02/082514	10/17/2002	WO				N	Y
	B44	02/13262	02/14/2002	WO				N	Y
	B45	02/15244	02/21/2002	WO				N	Y
	B46	02/27783	04/04/2002	WO				N	Y
Lee	B47	02/47168	06/13/2002	WO				N	Y
	B48	03/015140	02/20/2003	WO				N	Y
OTHER ART, JOURNAL ARTICLES, ETC.									
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
Lee	C1	Armstrong <i>et al.</i> , "Design of Si/SiGe Heterojunction Complementary Metal-Oxide-Semiconductor Transistors," <u>IEDM Technical Digest (1995 International Electron Devices Meeting)</u> , pp. 761-764.							
	C2	Armstrong, "Technology for SiGe Heterostructure-Based CMOS Devices," PhD Thesis, Massachusetts Institute of Technology, 1999, pp. 1-154.							
	C3	Augusto <i>et al.</i> , "Proposal for a New Process Flow for the Fabrication of Silicon-Based Complementary MOD-MOSFETs without Ion Implantation," <u>Thin Solid Films</u> , Vol. 294, No. 1-2 (February 15, 1997), pp. 254-258.							
	C4	Barradas <i>et al.</i> , "RBS analysis of MBE-grown SiGe/(001) Si heterostructures with thin, high Ge content SiGe channels for HMOS transistors," <u>Modern Physics Letters B</u> , Vol. 15 (2001), abstract.							
	C5	Borenstein <i>et al.</i> , "A New Ultra-Hard Etch-Stop Layer for High Precision Micromachining," Proceedings of the 1999 12th IEEE International Conference on Micro Electro Mechanical Systems (MEMS) (January 17-21, 1999), pp. 205-210.							
	C6	Bouillon <i>et al.</i> , "Search for the optimal channel architecture for 0.18/0.12 μ m bulk CMOS experimental study," <u>IEEE</u> (1996), pp. 21.2.1-21.2.4.							
EXAMINER	Lee				DATE CONSIDERED 9/23/04				



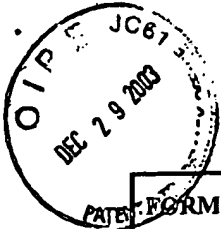
FORM PTO - 1449		ATTORNEY DOCKET NO.: ASC-058A
INFORMATION DISCLOSURE STATEMENT		APPLICANT(S): Leitz <i>et al.</i>
		SERIAL NO.: 10/647,074
		FILING DATE: August 22, 2003 GROUP: 2812-2823
OTHER ART, JOURNAL ARTICLES, ETC.		
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)	
La	C7	Bruel <i>et al.</i> , "@SMART CUT: A Promising New SOI Material Technology," Proceedings of the 1995 IEEE International SOI Conference (October 1995), pp. 178-179.
	C8	Bruel, "Silicon on Insulator Material Technology," <u>Electronic Letters</u> , Vol. 13, No. 14 (July 6, 1995), pp. 1201-1202.
	C9	Bufler <i>et al.</i> , "Hole transport in strained Si _{1-x} Ge _x alloys on Si _{1-y} Ge _y substrates," <u>Journal of Applied Physics</u> , Vol. 84, No. 10 (November 15, 1998), pp. 5597-5602.
	C10	Bulsara <i>et al.</i> , "Relaxed In _x Ga _{1-x} As Graded Buffers Grown with Organometallic Vapor Phase Epitaxy on GaAs," <u>Applied Physics Letters</u> , Vol. 72, Issue 13 (July 30, 1998), pp. 1608-1610.
	C11	Bulsara, "Materials Issues with the Integration of Lattice-Mismatched In _x Ga _{1-x} As on GaAs," PhD Thesis, MIT, June 1998, pp. 1-178.
	C12	Burghartz <i>et al.</i> , "Microwave Inductors and Capacitors in Standard Multilevel Interconnect Silicon Technology," <u>IEEE Transactions on Microwave Theory and Techniques</u> , Vol. 44, No. 1 (January 1996), pp. 100-104.
	C13	Buttard <i>et al.</i> , "Toward Two-Dimensional Self-Organization of Nanostructures Using Wafer Bonding and Nanopatterned Silicon Surfaces," <u>IEEE - 2002 Journal of Quantum Electronics</u> , Vol. 38, Issue 8 (August 2002), pp. 995-1005.
	C14	Canaperi <i>et al.</i> , "Preparation of a relaxed Si-Ge layer on an insulator in fabricating high-speed semiconductor devices with strained epitaxial films," International Business Machines Corporation, USA (2002), abstract.
	C15	Carlin <i>et al.</i> , "High Efficiency GaAs-on-Si Solar Cells with High Voc using Graded GeSi Buffers," <u>IEEE - 2000</u> (2000), pp. 1006-1011.
	C16	Carlin <i>et al.</i> , "Investigation and Development of High Quality GaAs-on-Si for Space Photovoltaics Using a Graded GeSi," PhD Thesis, Ohio State University, 2001, pp. 1-232.
	C17	Chang <i>et al.</i> , "Selective Etching of SiGe/Si Heterostructures," <u>Journal of the Electrochemical Society</u> , No. 1 (January 1991), pp. 202-204.
	C18	Charasse <i>et al.</i> , "MBE Growth of GaAs on Si at Thomson," <u>Institute of Electronic Structure and Laser</u>
	C19	Cheng <i>et al.</i> , "Electron Mobility Enhancement in Strained-Si n-MOSFETs Fabricated on SiGe-on-Insulator (SGOI) Substrates," <u>IEEE Electron Device Letters</u> , Vol. 22, No. 7 (July 2001), pp. 321-323.
La	C20	Cheng <i>et al.</i> , "Relaxed Silicon-Germanium on Insulator Substrate by Layer Transfer," <u>Journal of Electronic Materials</u> , Vol. 30, No. 12 (2001), pp. L37-L39.
EXAMINER	DATE CONSIDERED 9/23/04	



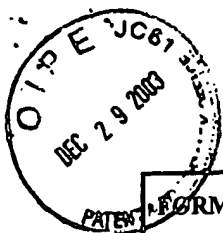
FORM PTO - 1449		ATTORNEY DOCKET NO.: ASC-058A	
INFORMATION DISCLOSURE STATEMENT		APPLICANT(S): Leitz <i>et al.</i>	
		SERIAL NO.: 10/647,074	
		FILING DATE: August 22, 2003 GROUP: 2842 3827	
OTHER ART, JOURNAL ARTICLES, ETC.			
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)		
La	C21	Crumbaker <i>et al.</i> , "The Influence of Dislocation Density on Electron Mobility in InP Films on Si," <u>Applied Physics Letters</u> , Vol. 59, Issue 9 (08/26/91), pp. 1090-1092.	
	C22	Cullis <i>et al.</i> , "Growth ripples upon strained SiGe epitaxial layers on Si and misfit dislocation interactions," <u>Journal of Vacuum Science and Technology A</u> , Vol. 12, No. 4 (July/August 1994), pp. 1924-1931.	
	C23	Currie <i>et al.</i> , "Carrier mobilities and process stability of strained Si n- and p-MOSFETs on SiGe virtual substrates," <u>Journal of Vacuum Science and Technology B</u> , Vol. 19, No. 6 (Nov/Dec 2001), pp. 2268-2279.	
	C24	Currie <i>et al.</i> , "Controlling Threading Dislocation Densities in Ge on Si Using Graded SiGe Layers and Chemical-Mechanical Polishing," <u>Applied Physics Letters</u> , Vol. 72, Issue 14 (04/06/98), pp. 1718-1720.	
	C25	Currie, "SiGe Virtual Substrate Engineering for Integration of III-V Materials, Microelectromechanical Systems and Strained Silicon Mosfets with Silicon," PhD Thesis, MIT, 2001, pp. 1-190.	
	C26	Dilliway <i>et al.</i> , "Characterization of Morphology and Defects in Silicon Germanium Virtual Substrates," <u>Journal of Materials Science</u> , Vol. 11, Issue 7 (2000), pp. 549-556.	
	C27	Eaglesham <i>et al.</i> , "Dislocation-Free Stranski-Krastanow Growth of Ge on Si(100)," <u>Physical Review Letters</u> , Vol. 64, No. 16 (April 16, 1990), pp. 1943-1946.	
	C28	Erdtmann <i>et al.</i> , "Gainas/Inp Quantum Well Infrared Photodetectors on Si Substrate for Low-Cost Focal Plan Arrays," PhD Thesis, Northwestern University, 2000, pp. 1-225.	
	C29	Feijoo <i>et al.</i> , "Epitaxial Si-Ge Etch Stop Layers with Ethylene Diamine Pyrocatechol for Bonded and Etchback Silicon-on-Insulator," <u>Journal of Electronic Materials</u> , Vol. 23, No. 6 (June 1994), pp. 493-496.	
	C30	Fischetti <i>et al.</i> , "Band structure, deformation potentials, and carrier mobility in strained Si, Ge, and SiGe alloys," <u>Journal of Applied Physics</u> , Vol. 80, No. 4 (August 15, 1996), pp. 2234-2252.	
	C31	Fischetti, "Long-range Coulomb interactions in small Si devices. Part II. Effective electron mobility in thin-oxide structures," <u>Journal of Applied Physics</u> , Vol. 89, No. 2 (January 15, 2001), pp. 1232-1250.	
	C32	Fitzgerald, "Dislocations in strained-layer epitaxy: theory, experiment, and applications," <u>Materials Science Reports</u> , Vol. 7 (1991), pp. 87-142.	
	C33	Fitzgerald <i>et al.</i> , "Dislocation dynamics in relaxed graded composition semiconductors," <u>Materials Science and Engineering</u> , B67 (1999), pp. 53-61.	
	C34	Fitzgerald <i>et al.</i> , "GeSi/Si Nanostructures," Department of Material Science, MIT (1995) pp 1-15	
	C35	Fitzgerald <i>et al.</i> , "Relaxed GexSi1-x structures for III-V integration with Si and high mobility two-dimensional electron gases in Si," <u>Journal of Vacuum Science Technology</u> , B 10(4) (Jul/August 1992), pp. 1807-1819.	
Lee	C36	Fitzgerald <i>et al.</i> , "Totally Relaxed GexSi1-x Layers with Low Threading Dislocation Densities Grown on Si Substrates," <u>Applied Physics Letters</u> , Vol. 59, No. 7 (August 12, 1991), pp. 811-813.	
EXAMINER		DATE CONSIDERED 9/23/04	



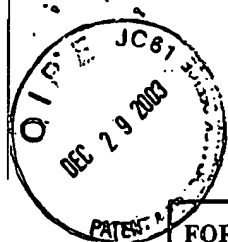
FORM PTO - 1449		ATTORNEY DOCKET NO.: ASC-058A	
INFORMATION DISCLOSURE STATEMENT		APPLICANT(S): Leitz <i>et al.</i>	
		SERIAL NO.: 10/647,074	
		FILING DATE: August 22, 2003 GROUP: 2842 2823	
OTHER ART, JOURNAL ARTICLES, ETC.			
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)		
Lee	C37	Garone <i>et al.</i> , "Silicon vapor phase epitaxial growth catalysis by the presence of germane," <u>Applied Physics Letters</u> , Vol. 56, No. 13 (March 26, 1990), pp. 1275-1277.	
	C38	Giovane <i>et al.</i> , "Strain-Balanced Silicon-Germanium Materials for Near IR Photodetection in Silicon-Based Optical Interconnects," PhD Thesis, MIT, 1998, pp. 1-134.	
	C39	Gray <i>et al.</i> , "Analysis and Design of Analog Integrated Circuits," John Wiley & Sons, 1984, pp. 605-632.	
	C40	Groenert <i>et al.</i> , "Strategies for Direct Monolithic Integration of Al _x Ga(1-x)As/In _x Ga(1-x)As LEDS and Lasers on Ge/GeSi/Si Substrates Via Relaxed Graded GexSi(1-x) Buffer Layers," <u>Materials Research Society Symposium Proceedings</u> , Vol. 692 (2002), pp. H.9.30.1-H.9.30.6.	
	C41	Grützmacher <i>et al.</i> , "Ge segregation in SiGe/Si heterostructures and its dependence on deposition technique and growth atmosphere," <u>Applied Physics Letters</u> , Vol. 63, No. 18 (November 1, 1993), pp. 2531-2533.	
	C42	Hackbarth <i>et al.</i> , "Alternatives to thick MBE-grown relaxed SiGe buffers," <u>Thin Solid Films</u> , Vol. 369, No. 1-2 (July 2000), pp. 148-151.	
	C43	Hackbarth <i>et al.</i> , "Strain relieved SiGe buffers for Si-based heterostructure field-effect transistors," <u>Journal of Crystal Growth</u> , Vol. 201/202 (1999), pp. 734-738.	
	C44	Herzog <i>et al.</i> , "SiGe-based FETs: buffer issues and device results," <u>Thin Solid Films</u> , Vol. 380 (2000), pp. 36-41.	
	C45	Höck <i>et al.</i> , "Carrier mobilities in modulation doped Si _{1-x} Gex heterostructures with respect to FET applications," <u>Thin Solid Films</u> , Vol. 336 (1998), pp. 141-144.	
	C46	Höck <i>et al.</i> , "High hole mobility in Si _{0.17} Ge _{0.83} channel metal-oxide-semiconductor field-effect transistors grown by plasma-enhanced chemical vapor deposition," <u>Applied Physics Letters</u> , Vol. 76, No. 26 (June 26, 2000), pp. 3920-3922.	
	C47	Höck <i>et al.</i> , "High performance 0.25 μ m p-type Ge/SiGe MODFETs," <u>Electronics Letters</u> , Vol. 34, No. 19 (September 17, 1998), pp. 1888-1889.	
	C48	Houghton, "Strain Relaxation Kinetics in Si _{1-x} Ge _x /Si Heterostructures," <u>Journal of Applied Physics</u> , Vol. 70, No. 4 (August 15, 1991), pp. 2136-2151.	
	C49	Hsu <i>et al.</i> , "Near Field Scanning Optical Microscopy Studies of Electronic and Photonic Materials and Devices," <u>Materials Science and Engineering Reports: A Review Journal</u> , Vol. 33 (2001), pp. 1-50.	
	C50	Huang <i>et al.</i> , "High-quality strain-relaxed SiGe alloy grown on implanted silicon-on-insulator substrate," <u>Applied Physics Letters</u> , Vol. 76, No. 19 (May 8, 2000), pp. 2680-2682.	
	C51	Huang <i>et al.</i> , "The Impact of Scaling Down to Deep Submicron on CMOS RF Circuits," <u>IEEE Journal of Solid-State Circuits</u> , Vol. 33, No. 7 (July 1998), pp. 1023-1036.	
	C52	Ishikawa <i>et al.</i> , "Creation of Si-Ge-based SIMOX structures by low energy oxygen implantation," <u>Proceedings of the 1997 IEEE International SOI Conference</u> (October 1997), pp. 16-17.	
Lee	C53	Ishikawa <i>et al.</i> , "SiGe-on-insulator substrate using SiGe alloy grown Si(001)," <u>Applied Physics Letters</u> , Vol. 75, No. 7 (August 16, 1999), pp. 983-985.	
EXAMINER		DATE CONSIDERED 9/23/04	



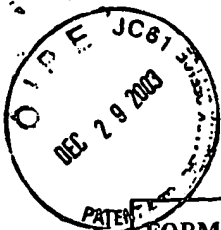
PATENT FORM PTO - 1449		ATTORNEY DOCKET NO.: ASC-058A	
INFORMATION DISCLOSURE STATEMENT		APPLICANT(S): Leitz <i>et al.</i>	
		SERIAL NO.: 10/647,074	
		FILING DATE: August 22, 2003 GROUP: 2842823	
OTHER ART, JOURNAL ARTICLES, ETC.			
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)		
Lee	C54	Ismail <i>et al.</i> , "Modulation-doped n-type Si/SiGe with inverted interface," <u>Applied Physics Letters</u> , Vol. 65, No. 10 (September 5, 1994), pp. 1248-1250.	
	C55	Ismail, "Si/SiGe High-Speed Field-Effect Transistors," Electron Devices Meeting, Washington, D.C. (December 10, 1995), pp. 20.1.1-20.1.4.	
	C56	Kearney <i>et al.</i> , "The effect of alloy scattering on the mobility of holes in a Si1-xGex quantum well," <u>Semiconductor Science and Technology</u> , Vol. 13 (1998), pp. 174-180.	
	C57	Kim <i>et al.</i> , "A Fully Integrated 1.9-GHz CMOS Low-Noise Amplifier," <u>IEEE Microwave and Guided Wave Letters</u> , Vol. 8, No. 8 (August 1998), pp. 293-295.	
	C58	Kissinger <i>et al.</i> , "Stepwise Equilibrated Graded GeSi1x Buffer with Very Low Threading Dislocation Density on Si(001)," <u>American Institute of Physics / Applied Physics Letters</u> , Vol. 66, Issue 16 (April 17, 1995), pp. 2083-2085.	
	C59	Knall <i>et al.</i> , "The Use of Graded in GaAs Layers and Patterned Substrates to Remove Threading Dislocations From GaAs on Si," <u>Journal of Applied Physics</u> , Vol. 76, Issue 5 (September 1, 1994), pp. 2697-2702.	
	C60	Koester <i>et al.</i> , "Extremely High Transconductance Ge/Si0.4Ge0.6 p-MODFET's Grown by UHV-CVD," <u>IEEE Electron Device Letters</u> , Vol. 21, No. 3 (March 2000), pp. 110-112.	
	C61	König <i>et al.</i> , "Design Rules for n-Type SiGe Hetero FETs," <u>Solid State Electronics</u> , Vol. 41, No. 10 (1997), pp. 1541-1547.	
	C62	König <i>et al.</i> , "p-Type Ge-Channel MODFET's with High Transconductance Grown on Si Substrates," <u>IEEE Electron Device Letters</u> , Vol. 14, No. 4 (April 1993), pp. 205-207.	
	C63	König <i>et al.</i> , "SiGe HBTs and HFETs," <u>Solid-State Electronics</u> , Vol. 38, No. 9 (1995), pp. 1595-1602.	
	C64	Kummer <i>et al.</i> , "Low energy plasma enhanced chemical vapor deposition," <u>Materials Science and Engineering</u> , B89 (2002), pp. 288-295.	
	C65	Kuznetsov <i>et al.</i> , "Technology for high-performance n-channel SiGe modulation-doped field-effect transistors," <u>Journal of Vacuum Science and Technology</u> , B 13(6) (November/December 1995), pp. 2892-2896.	
	C66	Langdo, "High Quality Ge on Si by Epitaxial Necking," <u>Applied Physics Letters</u> , Vol. 76, Issue 25 (June 19, 2000), pp. 3700-3702.	
	C67	Larson, "Integrated Circuit Technology Options for RFIC's Present Status and Future Directions," <u>IEEE Journal of Solid-State Circuits</u> , Vol. 33, No. 3 (March 1998), pp. 387-399.	
	C68	Lee <i>et al.</i> , "CMOS RF Integrated Circuits at 5 GHz and Beyond," <u>Proceedings of the IEEE</u> , Vol. 88, No. 10 (October 2000), pp. 1560-1571.	
	C69	Lee <i>et al.</i> , "Strained Ge channel p-type metal-oxide-semiconductor field-effect transistors grown on Si1-xGex/Si virtual substrates," <u>Applied Physics Letters</u> , Vol. 79, No. 20 (November 12, 2001), pp. 3344-3346.	
Lee	C70	Lee <i>et al.</i> , "Strained Ge channel p-type MOSFETs fabricated on Si1-xGex/Si virtual substrates," <u>Materials Research Society Symposium Proceedings</u> , Vol. 686 (2002), pp. A1.9.1-A1.9.5.	
EXAMINER		DATE CONSIDERED 9/23/04	



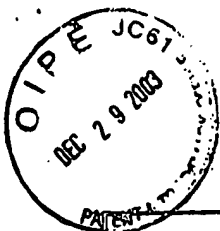
FORM PTO - 1449		ATTORNEY DOCKET NO.: ASC-058A	
INFORMATION DISCLOSURE STATEMENT		APPLICANT(S): Leitz <i>et al.</i>	
		SERIAL NO.: 10/647,074	
		FILING DATE: August 22, 2003 GROUP: 2812 2823	
OTHER ART, JOURNAL ARTICLES, ETC.			
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)		
Le	C71	LeGoues <i>et al.</i> , "Relaxation of SiGe Thin Films Grown on Si/SiO ₂ Substrates," <u>Journal of Applied Physics</u> , Vol. 75, Issue 11 (June 1, 1974), pp. 2730-2738.	
	C72	Leitz <i>et al.</i> , "Channel Engineering of SiGe-Based Heterostructures for High Mobility MOSFETs," <u>Materials Research Society Symposium Proceedings</u> , Vol. 686 (2002), pp. A3.10.1-A3.10.6.	
	C73	Leitz <i>et al.</i> , "Dislocation glide and blocking kinetics in compositionally graded SiGe/Si," <u>Journal of Applied Physics</u> , Vol. 90, No. 6 (September 15, 2001), pp. 2730-2736.	
	C74	Leitz <i>et al.</i> , "Hole mobility enhancements in strained Si/Si _{1-y} Ge _y p-type metal-oxide-semiconductor field-effect transistors grown on relaxed Si _{1-x} Ge _x (x<y) virtual substrates," <u>Applied Physics Letters</u> , Vol. 79, No. 25 (December 17, 2001), pp. 4246-4248.	
	C75	Li <i>et al.</i> , "Design of high speed Si/SiGe heterojunction complementary metal-oxide-semiconductor field effect transistors with reduced short-channel effects," <u>Journal of Vacuum Science and Technology A</u> , Vol. 20, No.3 (May/June 2002), pp. 1030-1033.	
	C76	Liu <i>et al.</i> , "Growth Study of Surfactant-Mediated Relaxed SiGe Graded Layers for 1.55- μ m Photodetector Applications," <u>Thin Solid Films</u> , Vol. 380, Issue 1-2 (2000), pp. 54-56.	
	C77	Liu <i>et al.</i> , "High-Quality Ge Films on Si Substrates Using SB Surfactant-Mediated Graded SiGe Buffers," <u>Applied Physics Letters</u> , Vol. 79, Issue 21 (November 19, 2001), pp. 3431-3433.	
	C78	Luan <i>et al.</i> , "High Quality Ge Epilayers on Si with Low Threading-Dislocations Densities," <u>Applied Physics Letters</u> , Vol. 75, Issue 19 (November 8, 1999), pp. 2909-2911.	
	C79	Lu <i>et al.</i> , "High Performance 0.1 μ m Gate-Length P-Type SiGe MODFET's and MOS-MODFET's," <u>IEEE Transactions on Electron Devices</u> , Vol. 47, No. 8 (August 2000), pp. 1645-1652.	
	C80	Luo <i>et al.</i> , "High-Quality Strain-Relaxed SiGe Films Grown with Low Temperature Si Buffer," <u>Journal of Applied Physics</u> , Vol. 89, Issue 13 (September 23, 1991), pp. 1611-1613.	
	C81	Maiti <i>et al.</i> , "Strained-Si heterostructure field effect transistors," <u>Semiconductor Science and Technology</u> , Vol. 13 (1998), pp. 1225-1246.	
	C82	Maszara, "Silicon-On-Insulator by Wafer Bonding: A Review," <u>Journal of the Electrochemical Society</u> , No. 1 (January 1991), pp. 341-347.	
	C83	Meyerson <i>et al.</i> , "Cooperative Growth Phenomena in Silicon/Germanium Low-Temperature Epitaxy," <u>Applied Physics Letters</u> , Vol. 53, No. 25 (December 19, 1988), pp. 2555-2557.	
	C84	Mizuno <i>et al.</i> , "Advanced SOI-MOSFETs with Strained-Si Channel for High Speed CMOS-Electron/Hole Mobility Enhancement," 2002 Symposium on VLSI Technology, Honolulu (June 13-15), <u>IEEE New York</u> , pp. 210-211.	
	C85	Mizuno <i>et al.</i> , "Electron and Hole Mobility Enhancement in Strained-Si MOSFET's on SiGe-on-Insulator Substrates Fabricated by SIMOX Technology," <u>IEEE Electron Device Letters</u> , Vol. 21, No. 5 (May 2000), pp. 230-232.	
Le	C86	Mizuno <i>et al.</i> , "High Performance Strained-Si p-MOSFETs on SiGe-on-Insulator Substrates Fabricated by SIMOX Technology," <u>IEEE IEDM Technical Digest</u> (1999 International Electron Device Meeting), pp. 934-936.	
EXAMINER		DATE CONSIDERED 9/23/04	



FORM PTO - 1449		ATTORNEY DOCKET NO.: ASC-058A	
INFORMATION DISCLOSURE STATEMENT		APPLICANT(S): Leitz <i>et al.</i>	
		SERIAL NO.: 10/647,074	
		FILING DATE: August 22, 2003 GROUP: 28122823	
OTHER ART, JOURNAL ARTICLES, ETC.			
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)		
Lee	C87	Momose <i>et al.</i> , "Dislocation-Free and Lattice-Matched Si/GAP1-xNx/Si Structure for Photo-Electronic Integrated Systems," <u>Applied Physics Letters</u> , Vol. 79, Issue 25 (December 17, 2001), pp. 4151-4153.	
	C88	Monroe <i>et al.</i> , "Comparison of Mobility-Limiting Mechanisms in High-Mobility Si1-xGex Heterostructures," <u>Journal of Vacuum Science and Technology B</u> , Vol. B11, Issue 4 (Jul/Aug 1993), pp. 1731-1737.	
	C89	Nayak <i>et al.</i> , "High-Mobility Strained-Si PMOSFET's," <u>IEEE Transactions on Electron Devices</u> , Vol. 43, No. 10 (October 1996), pp. 1709-1716.	
	C90	Oh <i>et al.</i> , "Interdigitated Ge P-I-N Photodetectors Fabricated on a Si Substrate Using Graded SiGe Buffer Layers," <u>IEEE - Journal of Quantum Electronics</u> , Vol. 38, Issue 9 (Sept 2002), pp. 1238-1241.	
	C91	Ohori <i>et al.</i> , "Effect of Threading Dislocations on Mobility in Selectively Doped Heterostructures Grown on Si Substrates," <u>Journal of Applied Physics</u> , Vol. 75, Issue 7 (April 1, 1994), pp. 3681-3683.	
	C92	O'Neill <i>et al.</i> , "SiGe virtual substrate N-channel heterojunction MOSFETS," <u>Semiconductor Science and Technology</u> , Vol. 14 (1999), pp. 784-789.	
	C93	Ota, "Application of heterojunction FET to power amplifier for cellular telephone," <u>Electronic Letters</u> , Vol. 30, No. 11 (May 26, 1994), pp. 906-907.	
	C94	Papananos, "Radio-Frequency Microelectronic Circuits for Telecommunication Applications," Kluwer Academic Publishers, 1999, pp. 115-117, 188-193.	
	C95	Parker <i>et al.</i> , "SiGe heterostructure CMOS circuits and applications," <u>Solid State Electronics</u> , Vol. 43 (1999), pp. 1497-1506.	
	C96	Powell <i>et al.</i> , "New Approach to the Growth of Low Dislocation Relaxed SiGe Material," <u>Applied Physics Letters</u> , Vol. 64, Issue 14 (April 4, 1994), pp. 1856-1858.	
	C97	Ransom <i>et al.</i> , "Gate-Self-Aligned n-channel and p-channel Germanium MOSFET's," <u>IEEE Transactions on Electron Devices</u> , Vol. 38, No. 12 (December 1991), pp. 2695.	
	C98	Reinking <i>et al.</i> , "Fabrication of high-mobility Ge p-channel MOSFETs on Si substrates," <u>Electronics Letters</u> , Vol. 35, No. 6 (March 18, 1999), pp. 503-504.	
	C99	Rim, "Application of Silicon-Based Heterostructures to Enhanced Mobility Metal-Oxide-Semiconductor Field-Effect Transistors," PhD Thesis, Stanford University, 1999, pp. 1-184.	
	C100	Rim <i>et al.</i> , "Enhanced Hole Mobilities in Surface-Channel Strained-Si p-MOSFETs," <u>IEDM</u> (1995), pp. 517-520.	
	C101	Rim <i>et al.</i> , "Fabrication and Analysis of Deep Submicron Strained-Si N-MOSFET's," <u>IEEE Transactions on Electron Devices</u> , Vol. 47, No. 7 (July 2000), pp. 1406-1415.	
	C102	Robbins <i>et al.</i> , "A model for heterogeneous growth of Si1-xGex films for hydrides," <u>Journal of Applied Physics</u> , Vol. 69, No. 6 (March 15, 1991), pp. 3729-3732.	
Lee	C103	Sadek <i>et al.</i> , "Design of Si/SiGe Heterojunction Complementary Metal-Oxide-Semiconductor Transistors," <u>IEEE Transactions on Electron Devices</u> (August 1996), pp. 1224-1232.	
EXAMINER		DATE CONSIDERED 9/23/04	



FORM PTO - 1449		ATTORNEY DOCKET NO.: ASC-058A	
INFORMATION DISCLOSURE STATEMENT		APPLICANT(S): Leitz <i>et al.</i>	
		SERIAL NO.: 10/647,074	
		FILING DATE: August 22, 2003 GROUP: 28422827	
OTHER ART, JOURNAL ARTICLES, ETC.			
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)		
Lee	C104	Sakaguchi <i>et al.</i> , "ELTRAN® by Splitting Porous Si Layers," Proceedings of the 195 th International SOI Symposium, Vol. 99-3 (1999), pp. 117-121.	
	C105	Sakai <i>et al.</i> , "Reduction of Threading Dislocation Density in SiGe Layers on Si (001) Using a Two-Step Strain - Relaxation Procedure," <u>Applied Physics Letters</u> , Vol. 79, Issue 21 (November 19, 2001), pp. 3398-3400.	
	C106	Samavedam <i>et al.</i> , "Novel Dislocation Structure and Surface Morphology Effects in Relaxed Ge/Si-Ge (graded) / Si Structures," <u>Journal of Applied Physics</u> , Vol. 87, Issue 7 (April 1, 1997), pp. 3108-3116.	
	C107	Schäffler, "High-Mobility Si and Ge Structures," <u>Semiconductor Science and Technology</u> , Vol. 12 (1997), pp. 1515-1549.	
	C108	Schimmel, "Defect Etch for <100> Silicon Evaluation," <u>Journal of the Electrochemical Society</u> , Vol. 126, No. 3 (March 1979), pp. 479-482.	
	C109	Sugimoto <i>et al.</i> , "A 2V, 500 MHz and 3V, 920 MHz Low-Power Current-Mode 0.6 μ m CMOS VCO Circuit," <u>IEICE Trans Electron</u> , Vol. E82-C, No. 7 (July 1999), pp. 1327-1329.	
	C110	Taylor <i>et al.</i> , "Optoelectronic Device Performance on Reduced Threading Dislocation Density GaAs/Si," <u>American Institute of Physics</u> , Vol. 89, Issue 8 (April 15, 2001), pp. 4365-4375.	
	C111	Tement <i>et al.</i> , "Metal Gate Strained Silicon MOSFETs for Microwave Integrated Circuits," <u>IEEE</u> (October 2000), pp. 38-43.	
	C112	Ting <i>et al.</i> , "Monolithic Integration of III-V Materials and Devices on Silicon," <u>SPIE Conference 1999- Silicon Based Optoelectronics</u> , Vol. 3630 (Jan 1999), pp. 19-28.	
	C113	Tsang <i>et al.</i> , "Measurements of alloy composition and strain in thin Ge _x Si _{1-x} layers," <u>Journal of Applied Physics</u> , Vol. 75, No. 12 (June 15, 1994), pp. 8098-8108.	
	C114	Tweet <i>et al.</i> , "Factors determining the composition of strained GeSi layers grown with disilane and germane," <u>Applied Physics Letters</u> , Vol. 65, No. 20 (November 14, 1994), pp. 2579-2581.	
	C115	Usami <i>et al.</i> , "Spectroscopic study of Si-based quantum wells with neighboring confinement structure," <u>Semiconductor Science and Technology</u> , (1997), abstract.	
	C116	Valtueña <i>et al.</i> , "Influence of the Surface Morphology on the Relaxation of Low-Strained In _x Ga _{1-x} As Linear Buffer Structures," <u>Journal of Crystal Growth</u> , Vol. 182 (1997), pp. 281-291.	
	C117	Watson <i>et al.</i> , "Relaxed, Low Threading Defect Density Si _{0.7} Ge _{0.3} Epitaxial Layers Grown on Si by Rapid Thermal Chemical Vapor Deposition," <u>Journal of Applied Physics</u> , Vol. 75, Issue 1 (January 1, 1994), pp. 263-269.	
	C118	Welser <i>et al.</i> , "Electron Mobility Enhancement in Strained-Si N-Type Metal-Oxide-Semiconductor Field-Effect Transistors," <u>IEEE Electron Device Letters</u> , Vol. 15, No. 3 (March 1994), pp. 100-102.	
Lee	C119	Welser <i>et al.</i> , "Evidence of Real-Space Hot-Electron Transfer in High Mobility, Strained-Si Multilayer MOSFETs," <u>IEEE IDEM Technical Digest</u> (1993 International Electron Devices Meeting), pp. 545-548.	
EXAMINER		DATE CONSIDERED	
Lee		9/23/04	



FORM PTO - 1449		ATTORNEY DOCKET NO.: ASC-058A	
INFORMATION DISCLOSURE STATEMENT		APPLICANT(S): Leitz <i>et al.</i>	
		SERIAL NO.: 10/647,074	
		FILING DATE: August 22, 2003 GROUP: 2812823	
OTHER ART, JOURNAL ARTICLES, ETC.			
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)		
Lee	C120	✓ Welser <i>et al.</i> , "NMOS and PMOS Transistors Fabricated in Strained Silicon/Relaxed Silicon-Germanium Structures," <u>IEEE JDEM Technical Digest</u> (1992 International Electron Devices Meeting), pp. 1000-1002.	
	C121	✓ Welser, "The Application of Strained Silicon/Relaxed Silicon Germanium Heterostructures to Metal-Oxide-Semiconductor Field-Effect Transistors," PhD Thesis, Stanford University, 1994, pp. 1-205.	
	C122	✓ Wolf <i>et al.</i> , "Silicon Processing for the VLSI Era, Vol. 1: Process Technology," Lattice Press, Sunset Beach, CA, 1986, pp. 384-386.	
	C123	✓ Xie <i>et al.</i> , "Fabrication of High Mobility Two-Dimensional Electron and Hole Gases in GeSi/Si," <u>Journal of Applied Physics</u> , Vol. 73, Issue 12 (June 15, 1993), pp. 8364-8370.	
	C124	✓ Xie <i>et al.</i> , "Semiconductor Surface Roughness: Dependence on Sign and Magnitude of Bulk Strain," <u>The Physical Review Letters</u> , Vol. 73, No. 22 (November 28, 1994), pp. 3006-3009.	
	C125	✓ Xie <i>et al.</i> , "Very High Mobility Two-Dimensional Hole Gas in Si/GexSi1-x/Ge Structures Grown by Molecular Beam Epitaxy," <u>Applied Physics Letters</u> , Vol. 63, Issue 16 (October 18, 1993), pp. 2263-2264.	
	C126	✓ Xie, "SiGe Field Effect Transistors," <u>Materials Science and Engineering</u> , Vol. 25 (1999), pp. 89-121.	
	C127	✓ Yamagata <i>et al.</i> , "Bonding, Splitting and Thinning by Porous Si in ELTRAN®; SOI-Epi Wafer™," <u>Materials Research Society Symposium Proceedings</u> , Vol. 681E (2001), pp. 18.2.1-18.2.10.	
	C128	✓ Yeo <i>et al.</i> , "Nanoscale Ultra-Thin-Body Silicon-on-Insulator P-MOSFET with a SiGe/Si Heterostructure Channel," <u>IEEE Electron Device Letters</u> , Vol. 21, No. 4 (April 2000), pp. 161-163.	
	C129	✓ Zhang <i>et al.</i> , "Demonstration of a GaAs-Based Compliant Substrate Using Wafer Bonding and Substrate Removal Techniques," <u>Electronic Materials and Processing Research Laboratory, Department of Electrical Engineering, University Park, PA 16802</u> , 1998, pp. 25-28.	
	C130	✓ "Optimal Growth Technique and Structure for Strain Relaxation of Si-Ge Layers on Si Substrates," <u>IBM Technical Disclosure Bulletin</u> , Vol. 32, No. 8A (January 1990), pp. 330-331.	
Lee	C131	✓ "2 Bit/Cell EEPROM Cell Using Band to Band Tunneling for Data Read-Out," <u>IBM Technical Disclosure Bulletin</u> , Vol. 35, No. 4B (September 1992), pp. 136-140.	
EXAMINER		DATE CONSIDERED	
[Signature]		9/23/2004	